# Focussed Ion-Beams for Nanofabrication of Superconducting Devices: Josephson Arrays, Nanowires and Flux-Tuneable r.f. Resonators

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# Nanofabrication at UCL



- Two Zeiss "cross-beam" Ga FIBs
- Zeiss Ne / He FIB



Raith 150<sup>TWO</sup> 30 kV EBL
Elionix 100 kV EBL







# Which Beam to Use?



	Neon FIB	Gallium FIB	Helium FIB	E-Beam Lithography	EUV Optical Lithography
Cost (order of magnitude, £)	10 <sup>6</sup>	10 <sup>6</sup>	10 <sup>6</sup>	10 <sup>6</sup>	10 <sup>8</sup>
Minimum feature size (nm)	6	30	6	10	20
Sample poisoning	Acceptable	Bad	Acceptable	Excellent	Excellent
Fabrication throughput	Good	Very good	Poor	Very good	Excellent
Ease of 3-D fabrication	Good	Good	Good	Limited	Limited
Cost of process	Minimal	Minimal	Minimal	High	High
Compatability with silicon	Yes	Yes	No	Yes	Yes

Conventional mantra for Ga-FIB:

"Always use EBL unless there is a compelling reason not to!"

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#### e.g.: Three-Dimensional Nanofabrication

# **Does the mantra change for Neon-FIB?**

# Format of this Talk



• Three-dimensional nanofabrication with Ga-FIB

process variability, sample damage...

• Neon-FIB

(i) Tuneable niobium r.f. resonators for spin qubit readout

(ii) NbN coherent quantum phase-slip nanowires

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# **3-D Ga-FIB Nanofabrication**





Tl<sub>2</sub>Ba<sub>2</sub>CaCu<sub>2</sub>O<sub>8</sub> intrinsic junction stack by lateral Ga-FIB milling

ZnO tetrapod: four-terminal superconducting contacts by Ga-FIB deposition

# Ga Implantation in TI2Ba2CaCu2O8



#### **Ga-FIB-Deposited Nanomechanics**



#### **Radially-Varying Young's Modulus**



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# **Readout of Spin Qubits**



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# Can we make the superconducting resonator *tuneable*?





# **Tuneable Readout of Spin Qubits**



#### Challenge: High Q in field up to ~ 100 mT

e.g. clock transitions in Bi-doped Si – Wolfowicz et al. Nature Nanotech. 8 561 (2013)

**UCL** 

# Milling with Neon

	helium	neon	gallium
Au Sputter yield (30 kV)	0.153	I.78	3.9
Al Sputter yield (30 kV)	0.06	4.39	17.4
Current	0.1 - 2 pA	0.2 - 5 pA	I pA - 100 nA
Minimum beam diameter	0.5 nm	2 nm	5 nm
Sample damage	Amorphisation	Amorphisation	Amorphisation and <b>poisoning</b>
Min Feature size	<10nm?	<20nm	20-40nm

#### **EBL / Neon-FIB Mix-and-Match**

(a)



O.W. Kennedy, PAW et al. Phys. Rev. App. 11, 014006 (2019)

#### **Nb Tuneable Resonator**



T = 300 mK  $\Delta f_0/f_0$  = 0.81% in 10 μT Q = 25,000 Flux focussing factor: 124 β<sub>L</sub>>3.4

#### **Nb Tuneable Resonator**



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# **Coherent Quantum Phase-Slip**

#### **Josephson Junction**



Coherent tunnelling of electric charge through the insulating barrier

# **Coherent Quantum Phase-Slip**

#### **Josephson Junction**



#### Quantum Phase-Slip Nanowire



Coherent tunnelling of electric charge through the insulating barrier

Coherent tunnelling of *magnetic flux* through the *superconducting* barrier

# **Coherent Quantum Phase-Slip**

#### **Josephson Junction**



#### **Quantum Phase-Slip Nanowire**



Coherent tunnelling of electric charge through the insulating barrier

Coherent tunnelling of *magnetic flux* through the *superconducting* barrier

.... Requires highly disordered superconductor

#### **Coherent Quantum Phase-Slip**



# Embedding Nanowires in Resonators



# Nanowire Width = 100 nm

J. Burnett, PAW et al. Phys. Rev. App. 8, 014039 (2017)



Q ≈ 1000

#### Nanowire Width = 35 nm

#### Evidence of incoherent quantum phase slips



# Conclusions

• Neon-FIB milling for Nb Dayem bridges

Resonator Q > 10,000 for fields up to 60 mT

• Neon-FIB milling for NbN nanowires

Resonator  $Q \sim 1,000$ 

Smaller dimensions and lower T needed for CQPS





# Acknowledgements

Marion Sourribes Huan Wang Sajid Saleem Jon Fenton Nic Constantino Jonathan Burnett **Oscar Kennedy** Jamie Potter





Engineering and Physical Sciences Research Council



The Leverhulme Trust

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